

A₁ member 24.”

Replace the paragraph beginning on page 7, line 26 with the following paragraph:

A₂ “In the resist mask 26, an opening 26a is formed with a diameter D1 of 0.2~0.3 μ m, for example, which substantially corresponds to the width of the electrode member 24. The reactive ion etching unit 10 is used to remove a region of the insulating layer 23 exposed through the opening 26a to thereby form an etched hole 27 leading to the electrode member 24. For a selective etching process to form the etched hole 27, the semiconductor device is placed on the sample holder 19 such that the surface 23a of the insulating layer 23 faces the upper electrode 15 of the reactive ion etching unit 10.”

Replace the paragraph beginning on page 9, line 25 with the following paragraph:

A₃ “The etching stop phenomenon was observed during a one-minute etching process at a point indicated by a code 28a on the characteristic curve 28 and at a point indicated by a code 29a on the characteristic curve 29, but the etching stop phenomenon did not take place at any other points on the other characteristic curves.”

Replace the paragraph beginning on page 10, line 18 with the following

paragraph:

A4 "Referring back to Fig. 1(c), a distance H from the upper surface of the electrode member 24 to the lower electrode member 25 is generally larger than 300nm."

Replace the paragraph beginning on page 10, line 21 with the following

paragraph:

A5 "Therefore, if the permissible placement error of the resist mask 26 is limited to 0.04 μ m and the resist mask 26 is placed properly within this error limit, by performing the etching process to the insulating layer 23 under the condition that the reaction chamber pressure is maintained at 100mTorr or higher while supplying the reaction chamber 11 of the reactive ion etching unit 10 with a mixed reaction gas of CHF₃ and CO at a flow ratio of about 15/85 for these component gases, as shown in Fig. 1(c), the unaligned portion due to the offset \underline{s} of the etched hole 27 never reaches the lower electrode member 25 even if there is an offset within the permissible error."

Replace the paragraph beginning on page 11, line 17 with the following

paragraph:

A6 "Fig. 4 is a graph (2) obtained from results of an experiment to find the etching stop condition, in which, as in the graph (1) of Fig. 3, the horizontal axis denotes offsets \underline{s} (in μ m) of the resist mask 26 and the vertical axis denotes depths \underline{d} (in nm) (see Fig. 1(c)) of the unaligned portion of the etched hole 27 from the upper surface of the